

### 1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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WeEn Semiconductors



**Product data sheet** 

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring direct interfacing to logic level ICs and low power gate drivers.

### 2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	8	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	-	1	Α
Static characte	eristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	3	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	5	mA

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2—T1
2	T2	main terminal 2		sym051
3	G	gate		,
4	T2	main terminal 2	☐1 ☐2 ☐3 SC-73 (SOT223)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
Z0103NN	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

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# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	1	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	8	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	8.5	Α
I <sup>2</sup> t	I2t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.32	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/µs; T2+ G+	-	50	A/µs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/ $\mu$ s; T2+ G-	-	50	A/µs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/µs; T2- G-	-	50	A/µs
		$I_T = 1 \text{ A}$ ; $I_G = 20 \text{ mA}$ ; $dI_G/dt = 0.1 \text{ A/}\mu\text{s}$ ; T2- G+	-	20	A/µs
I <sub>GM</sub>	peak gate current		-	1	Α
P <sub>GM</sub>	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C

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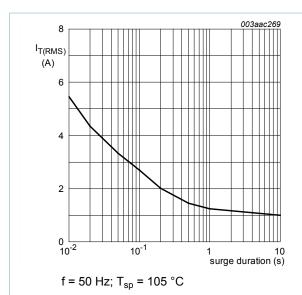


Fig. 1. RMS on-state current as a function of surge duration; maximum values

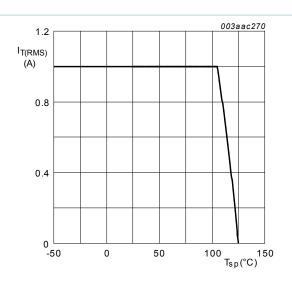
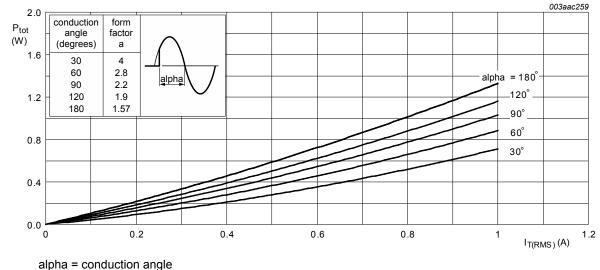


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values



 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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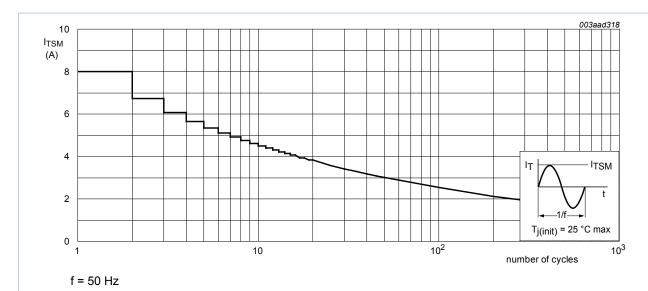
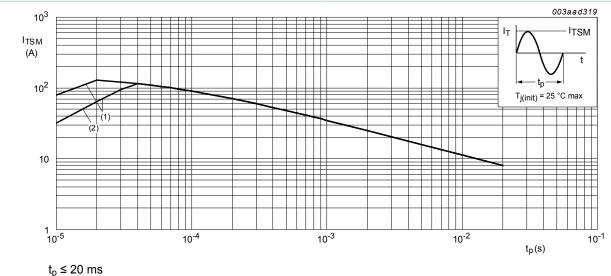


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum



- (1) dI<sub>T</sub>/dt limit
- (2) T2- G+ quadrant limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	full cycle; Fig. 8	-	-	15	K/W
uig-a)	thermal resistance from junction to	full cycle; printed circuit board mounted: minimum footprint; Fig. 6	-	156	-	K/W
	ambient	full cycle; printed circuit board mounted: pad area; Fig. 7	-	70	-	K/W

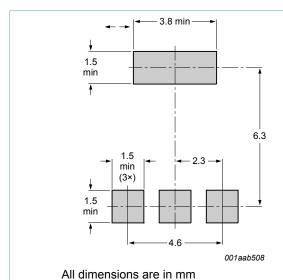
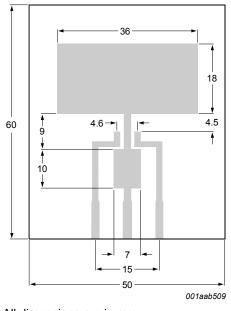


Fig. 6. Minimum footprint SOT223



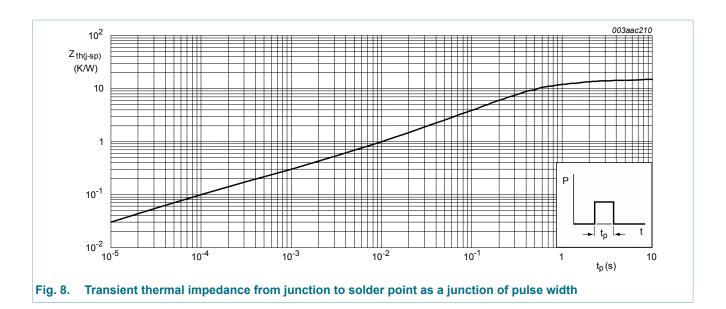
All dimensions are in mm

Printed circuit board:

FR4 epoxy glass (1.6 mm thick), copper laminate (35 um thick)

Fig. 7. Printed circuit board pad area: SOT223

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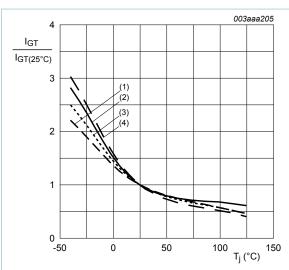
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## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics		·			
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 9}}$	-	-	3	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	5	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 10}}$	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 10}}$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 10}}$	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 10}}$	-	-	7	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	-	7	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 13	-	-	1	V
		$V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 13	0.2	-	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	-	0.5	mA
Dynamic	characteristics	1		-	-	
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 14	10	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 110 \text{ °C}; \text{ dI}_{com}/$ dt = 0.44 A/ms; gate open circuit	0.5	-	-	V/µs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

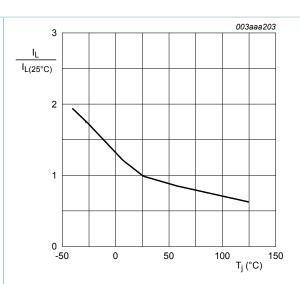


Fig. 10. Normalized latching current as a function of junction temperature

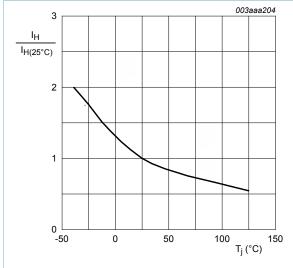
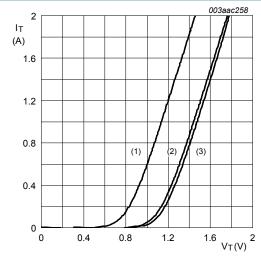


Fig. 11. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$ 

 $R_s = 0.31 \Omega$ 

(1) T<sub>i</sub> = 125 °C; typical values

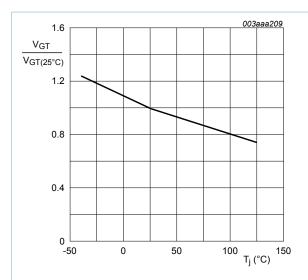
(2) T<sub>i</sub> = 125 °C; maximum values

(3) T<sub>j</sub> = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

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junction temperature

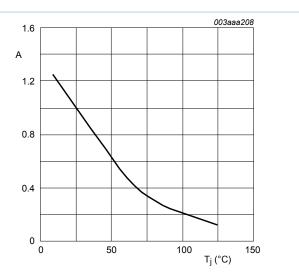
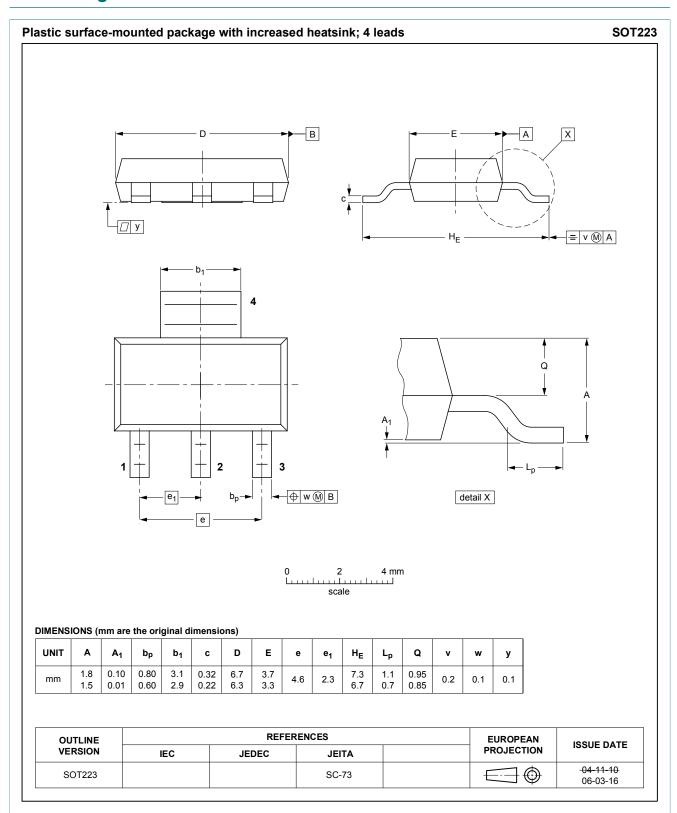


Fig. 13. Normalized gate trigger voltage as a function of Fig. 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

$$A = \frac{d\mathrm{V}_{\mathrm{D}(\mathrm{Tj}\,^{\circ}\,\mathrm{C})}\,/\,\,dt}{d\mathrm{V}_{\mathrm{D}(25\,^{\circ}\,\mathrm{C})}/\,\,dt}$$

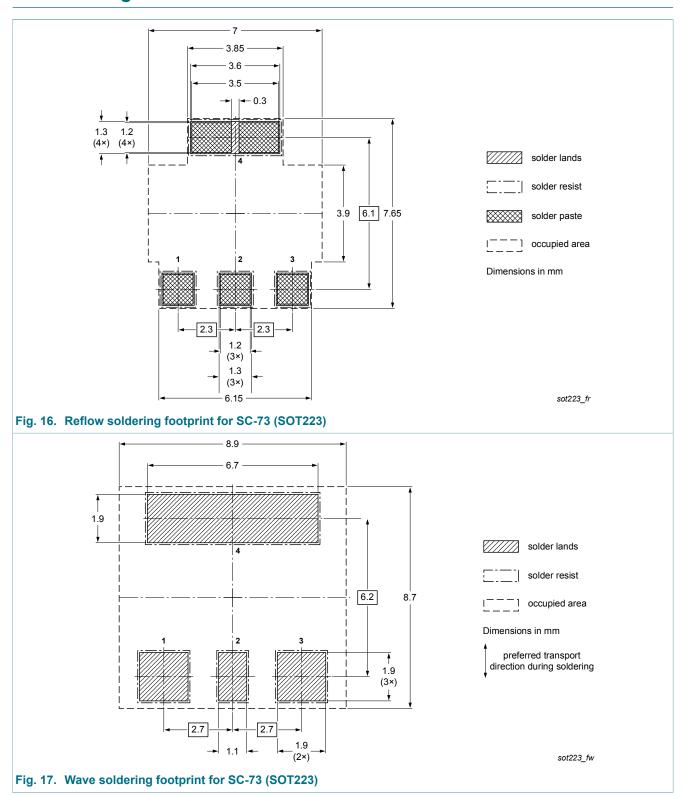
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## 10. Package outline



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## 11. Soldering



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## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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